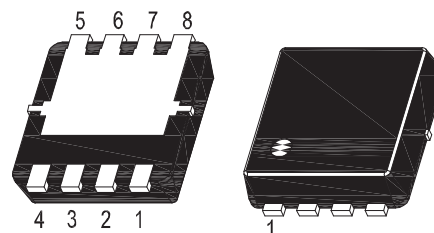
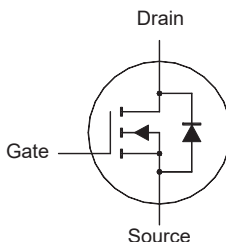


## N-Channel Enhancement Mode MOSFET

### Features

- Low  $R_{DS(ON)}$
- Halogen and Antimony Free(HAF), RoHS compliant



1. Source 2. Source 3. Source 4. Gate  
5. Drain 6. Drain 7. Drain 8. Drain  
DFN3030 Plastic Package

### Application

- DC-DC converters

### Key Parameters

| Parameter        | Value                  | Unit       |
|------------------|------------------------|------------|
| $BV_{DSS}$       | 30                     | V          |
| $R_{DS(ON)}$ Max | 6 @ $V_{GS} = 10$ V    | m $\Omega$ |
|                  | 9 @ $V_{GS} = 4.5$ V   |            |
| $V_{GS(th)}$ typ | 1.7                    | V          |
| $Q_g$ typ        | 46.6 @ $V_{GS} = 10$ V | nC         |

### Absolute Maximum Ratings (at $T_a = 25^\circ\text{C}$ unless otherwise specified)

| Parameter                                        | Symbol         | Value         | Unit             |
|--------------------------------------------------|----------------|---------------|------------------|
| Drain-Source Voltage                             | $V_{DS}$       | 30            | V                |
| Gate-Source Voltage                              | $V_{GS}$       | $\pm 20$      | V                |
| Continuous Drain Current                         | $I_D$          | 60            | A                |
|                                                  |                | 38            |                  |
| Peak Drain Current, Pulsed <sup>1)</sup>         | $I_{DM}$       | 240           | A                |
| Avalanche Current                                | $I_{AS}$       | 38.5          | A                |
| Single Pulse Avalanche Energy <sup>2)</sup>      | $E_{AS}$       | 74.1          | mJ               |
| Total Power Dissipation                          | $P_{tot}$      | 26            | W                |
| Operating Junction and Storage Temperature Range | $T_J, T_{stg}$ | - 55 to + 150 | $^\circ\text{C}$ |

### Thermal Characteristics

| Parameter                                                 | Symbol          | Max. | Unit               |
|-----------------------------------------------------------|-----------------|------|--------------------|
| Thermal Resistance from Junction to Case                  | $R_{\theta JC}$ | 4.8  | $^\circ\text{C/W}$ |
| Thermal Resistance from Junction to Ambient <sup>3)</sup> | $R_{\theta JA}$ | 60   | $^\circ\text{C/W}$ |

<sup>1)</sup> Pulse Test: Pulse Width  $\leq 100$   $\mu\text{s}$ , Duty Cycle  $\leq 2\%$ , Repetitive rating, pulse width limited by junction temperature  $T_{J(MAX)} = 150^\circ\text{C}$ .

<sup>2)</sup> Limited by  $T_{J(MAX)}$ , starting  $T_J = 25^\circ\text{C}$ ,  $L = 0.1$  mH,  $R_g = 25$   $\Omega$ ,  $I_{AS} = 38.5$  A,  $V_{GS} = 10$  V.

<sup>3)</sup> Device mounted on FR-4 substrate PC board, 2oz copper, with 1-inch square copper plate in still air.

Characteristics at  $T_a = 25^\circ\text{C}$  unless otherwise specified

| Parameter                                                                                                                                                                        | Symbol       | Min.   | Typ.       | Max.      | Unit          |
|----------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|--------------|--------|------------|-----------|---------------|
| <b>STATIC PARAMETERS</b>                                                                                                                                                         |              |        |            |           |               |
| Drain-Source Breakdown Voltage<br>at $I_D = 250\ \mu\text{A}$                                                                                                                    | $BV_{DSS}$   | 30     | -          | -         | V             |
| Drain-Source Leakage Current<br>at $V_{DS} = 30\ \text{V}$                                                                                                                       | $I_{DSS}$    | -      | -          | 1         | $\mu\text{A}$ |
| Gate Leakage Current<br>at $V_{GS} = \pm 20\ \text{V}$                                                                                                                           | $I_{GSS}$    | -      | -          | $\pm 100$ | nA            |
| Gate-Source Threshold Voltage<br>at $V_{DS} = V_{GS}$ , $I_D = 250\ \mu\text{A}$                                                                                                 | $V_{GS(th)}$ | 1.0    | -          | 2.5       | V             |
| Drain-Source On-State Resistance<br>at $V_{GS} = 10\ \text{V}$ , $I_D = 20\ \text{A}$<br>at $V_{GS} = 4.5\ \text{V}$ , $I_D = 10\ \text{A}$                                      | $R_{DS(on)}$ | -<br>- | 4.3<br>-   | 6<br>9    | m $\Omega$    |
| <b>DYNAMIC PARAMETERS</b>                                                                                                                                                        |              |        |            |           |               |
| Forward Transconductance<br>at $V_{DS} = 5\ \text{V}$ , $I_D = 20\ \text{A}$                                                                                                     | $g_{fs}$     | -      | 35.5       | -         | S             |
| Gate resistance<br>at $V_{DS} = 0\ \text{V}$ , $V_{GS} = 0\ \text{V}$ , $f = 1\ \text{MHz}$                                                                                      | $R_g$        | -      | 4.5        | -         | $\Omega$      |
| Input Capacitance<br>at $V_{GS} = 0\ \text{V}$ , $V_{DS} = 15\ \text{V}$ , $f = 1\ \text{MHz}$                                                                                   | $C_{iss}$    | -      | 2280       | -         | pF            |
| Output Capacitance<br>at $V_{GS} = 0\ \text{V}$ , $V_{DS} = 15\ \text{V}$ , $f = 1\ \text{MHz}$                                                                                  | $C_{oss}$    | -      | 292        | -         | pF            |
| Reverse Transfer Capacitance<br>at $V_{GS} = 0\ \text{V}$ , $V_{DS} = 15\ \text{V}$ , $f = 1\ \text{MHz}$                                                                        | $C_{rss}$    | -      | 227        | -         | pF            |
| Gate charge total<br>at $V_{DS} = 15\ \text{V}$ , $I_D = 20\ \text{A}$ , $V_{GS} = 10\ \text{V}$<br>at $V_{DS} = 15\ \text{V}$ , $I_D = 20\ \text{A}$ , $V_{GS} = 4.5\ \text{V}$ | $Q_g$        | -<br>- | 46.6<br>23 | -<br>-    | nC            |
| Gate to Source Charge<br>at $V_{DS} = 15\ \text{V}$ , $I_D = 20\ \text{A}$ , $V_{GS} = 10\ \text{V}$                                                                             | $Q_{gs}$     | -      | 7.8        | -         | nC            |
| Gate to Drain Charge<br>at $V_{DS} = 15\ \text{V}$ , $I_D = 20\ \text{A}$ , $V_{GS} = 10\ \text{V}$                                                                              | $Q_{gd}$     | -      | 10.8       | -         | nC            |
| Turn-On Delay Time<br>at $V_{DD} = 15\ \text{V}$ , $I_D = 20\ \text{A}$ , $V_{GS} = 10\ \text{V}$ , $R_g = 3.3\ \Omega$                                                          | $t_{d(on)}$  | -      | 13         | -         | ns            |
| Turn-On Rise Time<br>at $V_{DD} = 15\ \text{V}$ , $I_D = 20\ \text{A}$ , $V_{GS} = 10\ \text{V}$ , $R_g = 3.3\ \Omega$                                                           | $t_r$        | -      | 40         | -         | ns            |
| Turn-Off Delay Time<br>at $V_{DD} = 15\ \text{V}$ , $I_D = 20\ \text{A}$ , $V_{GS} = 10\ \text{V}$ , $R_g = 3.3\ \Omega$                                                         | $t_{d(off)}$ | -      | 28         | -         | ns            |
| Turn-Off Fall Time<br>at $V_{DD} = 15\ \text{V}$ , $I_D = 20\ \text{A}$ , $V_{GS} = 10\ \text{V}$ , $R_g = 3.3\ \Omega$                                                          | $t_f$        | -      | 6          | -         | ns            |
| <b>Body-Diode PARAMETERS</b>                                                                                                                                                     |              |        |            |           |               |
| Drain-Source Diode Forward Voltage<br>at $I_S = 1\ \text{A}$ , $V_{GS} = 0\ \text{V}$                                                                                            | $V_{SD}$     | -      | -          | 1.2       | V             |
| Body-Diode Continuous Current                                                                                                                                                    | $I_S$        | -      | -          | 60        | A             |
| Body-Diode Continuous Current, Pulsed                                                                                                                                            | $I_{SM}$     | -      | -          | 240       | A             |
| Body Diode Reverse Recovery Time<br>at $I_S = 15\ \text{A}$ , $di/dt = 100\ \text{A} / \mu\text{s}$                                                                              | $t_{rr}$     | -      | 24         | -         | ns            |
| Body Diode Reverse Recovery Charge<br>at $I_S = 15\ \text{A}$ , $di/dt = 100\ \text{A} / \mu\text{s}$                                                                            | $Q_{rr}$     | -      | 13.6       | -         | nC            |

## Electrical Characteristics Curves

Fig. 1 Typical Output Characteristics

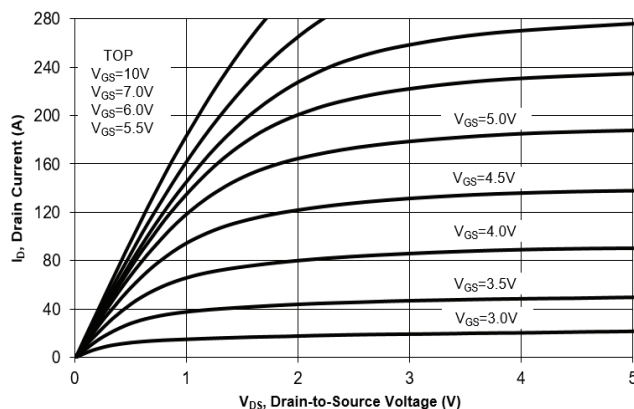


Fig. 2 Typical Transfer Characteristics

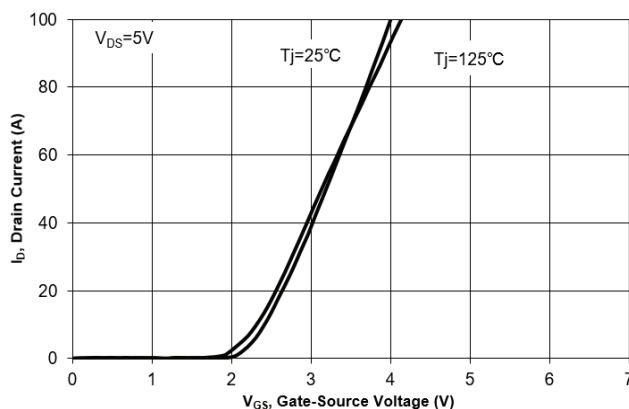


Fig. 3 on-Resistance vs. Drain Current

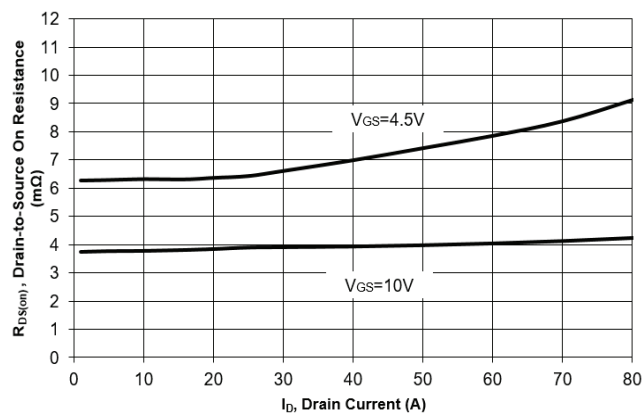


Fig. 4 on-Resistance vs. Gate to Source Voltage

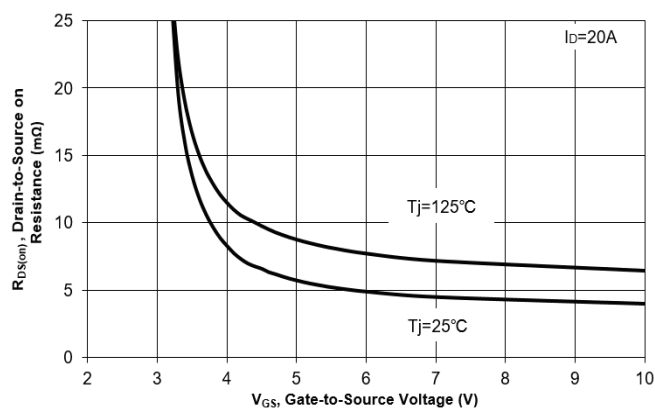


Fig. 5 on-Resistance vs.  $T_J$

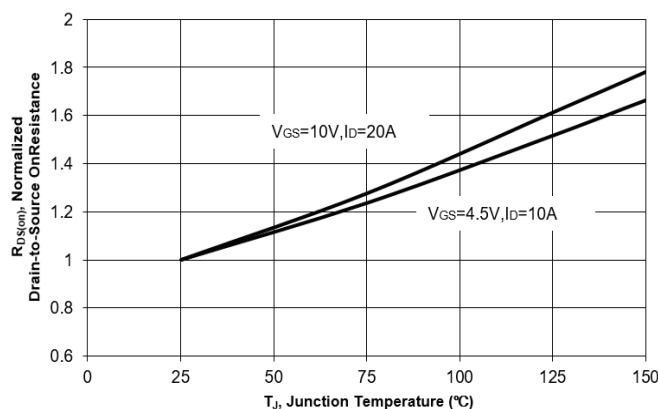
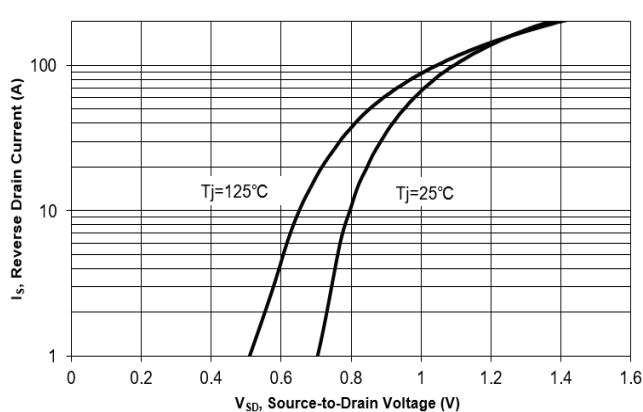


Fig. 6 Typical Body-Diode Forward Characteristics



## Electrical Characteristics Curves

Fig. 7 Typical Junction Capacitance

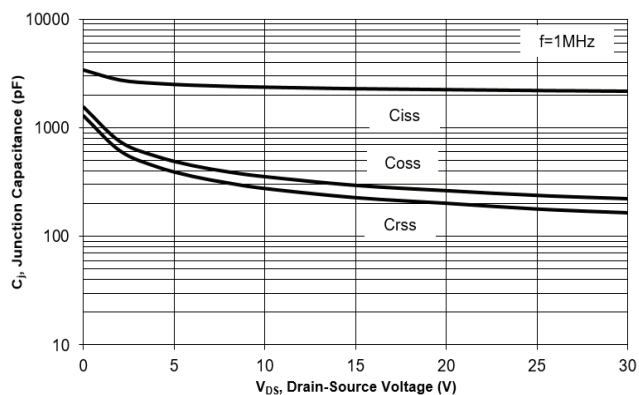


Fig. 8 Drain-Source Leakage Current vs.  $T_j$

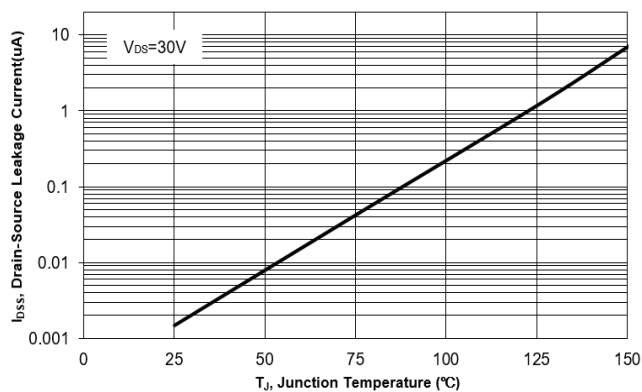


Fig. 9  $V_{(BR)DSS}$  vs. Junction Temperature

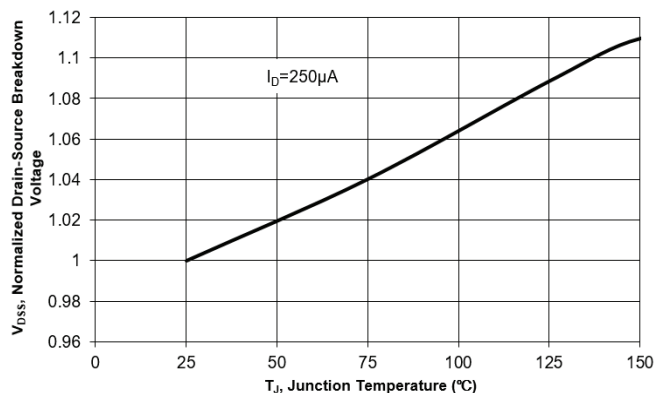


Fig. 10 Gate Threshold Variation vs.  $T_j$

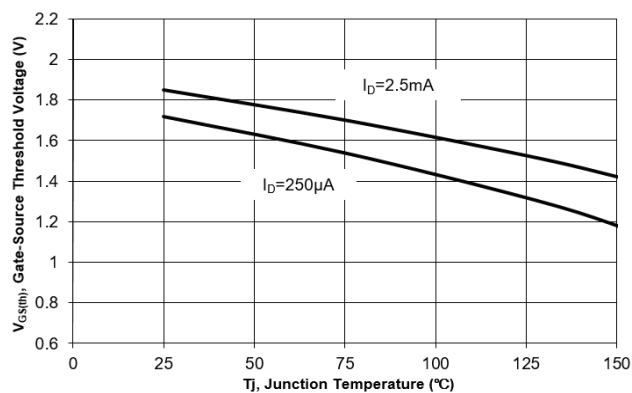


Fig. 11 Gate Charge

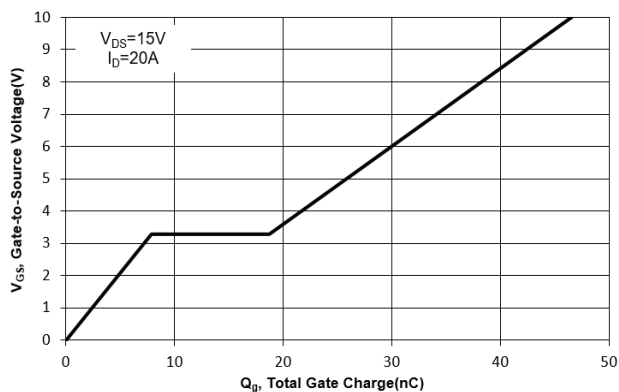
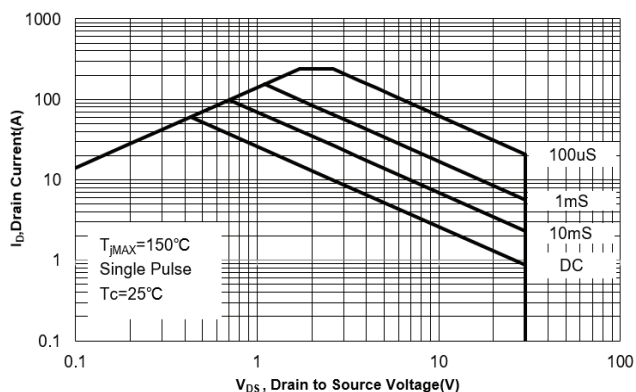


Fig. 12 Safe Operation Area



## Electrical Characteristics Curves

Fig. 13 Normalized Maximum Transient Thermal Impedance( $Z_{\theta JC}$ )

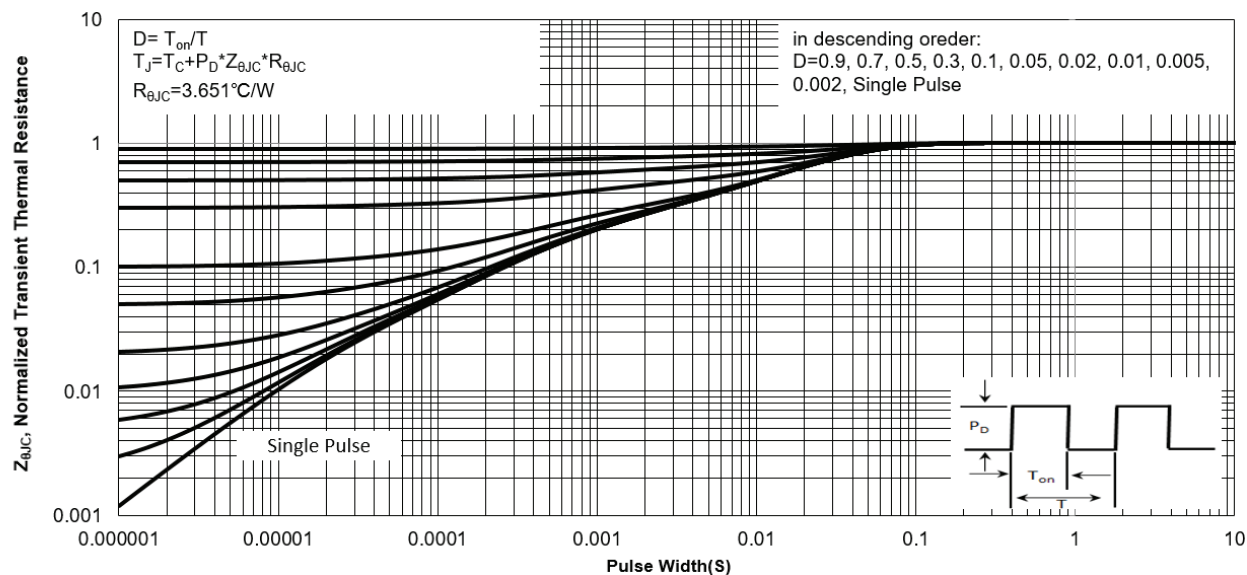
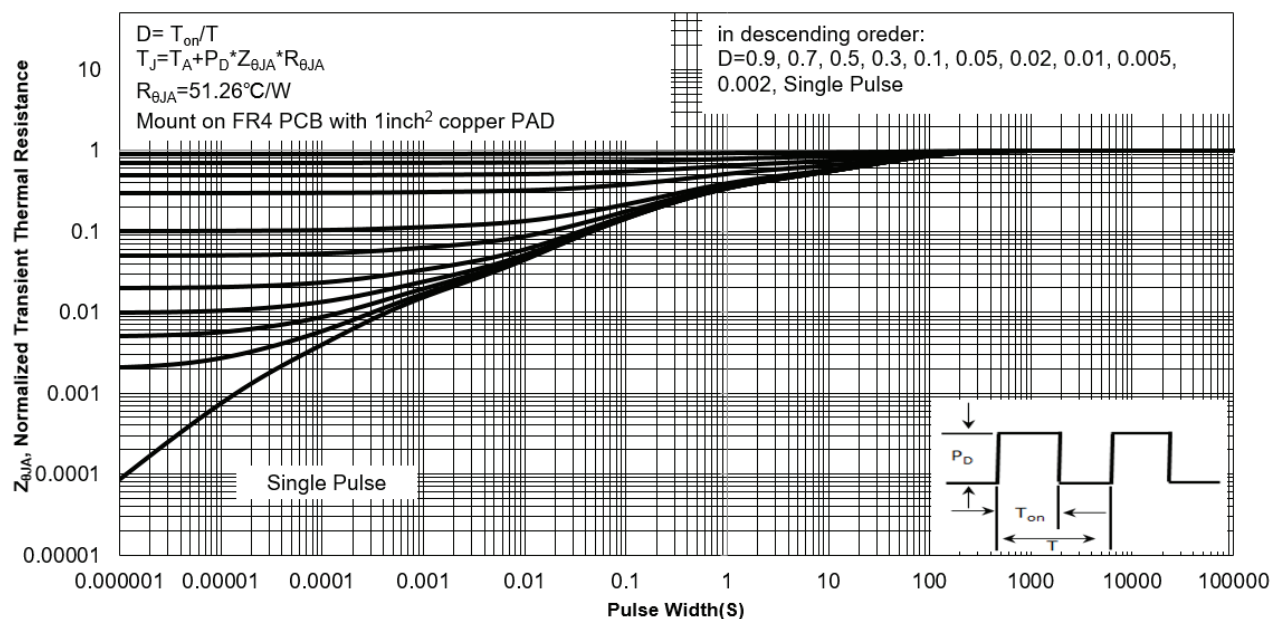
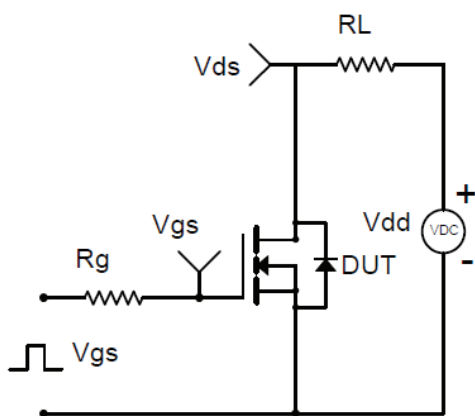
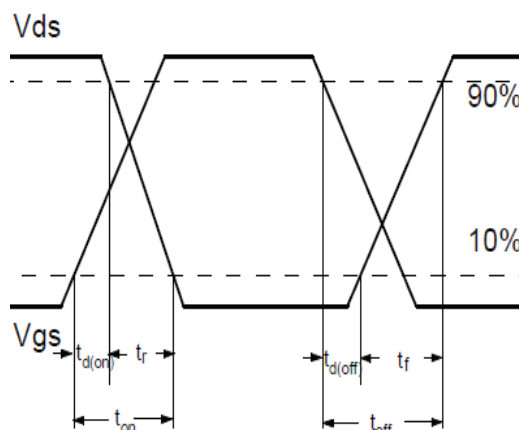
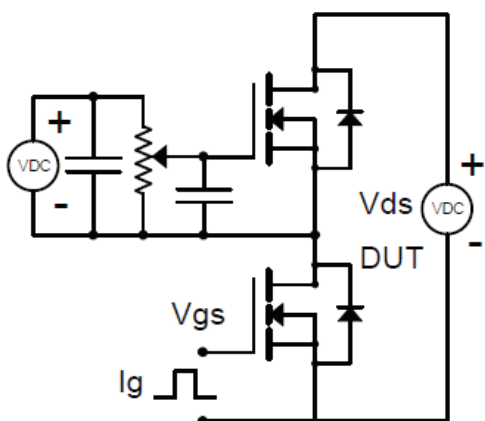
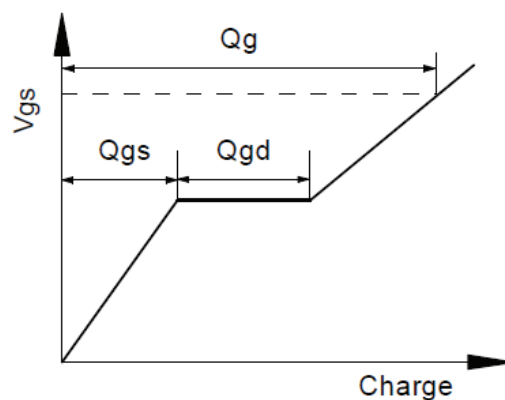
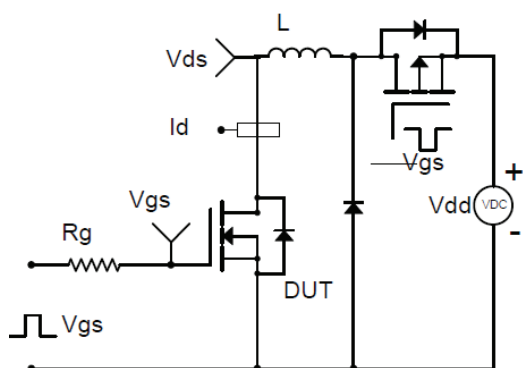
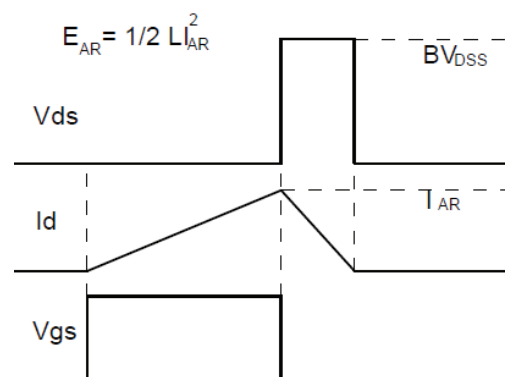


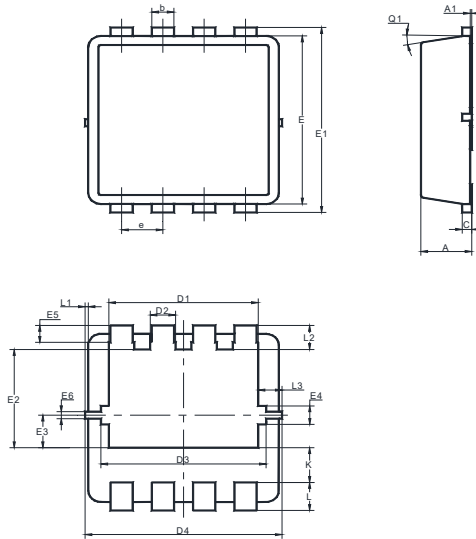
Fig. 14 Normalized Maximum Transient Thermal Impedance( $Z_{\theta JA}$ )



**Test Circuits**
**Fig.1-1 Switching times test circuit**

**Fig.1-2 Switching Waveform**

**Fig.2-1 Gate charge test circuit**

**Fig.2-2 Gate charge waveform**

**Fig.3-1 Avalanche test circuit**

**Fig.3-2 Avalanche waveform**


Package Outline Dimensions (Units: mm)

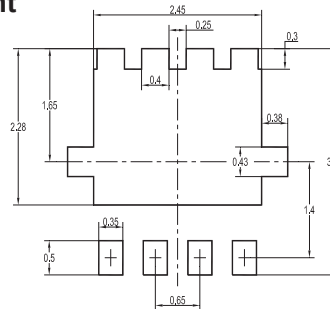
DFN3030



| UNIT | A   | A1   | b    | c    | D1  | D2  | D3  | D4  | E   | E1  | E2   | E3   | E4   |
|------|-----|------|------|------|-----|-----|-----|-----|-----|-----|------|------|------|
| mm   | 0.9 | 0.05 | 0.35 | 0.25 | 2.6 | 0.5 | 2.7 | 3.2 | 3.1 | 3.3 | 1.85 | 0.68 | 0.43 |
|      | 0.7 | 0    | 0.24 | 0.1  | 2.4 | 0.3 | 2.5 | 3   | 2.9 | 3.1 | 1.65 | 0.48 | 0.23 |

| UNIT | E5  | E6   | e   | K    | L   | L1  | L2   | L3    | θ1  |
|------|-----|------|-----|------|-----|-----|------|-------|-----|
| mm   | 0.4 | 0.25 | 0.7 | 0.72 | 0.5 | 0.1 | 0.53 | 0.475 | 12° |
|      | 0.2 | 0.15 | 0.6 | 0.52 | 0.3 | 0   | 0.33 | 0.275 | 0°  |

Recommended Soldering Footprint



Packing information

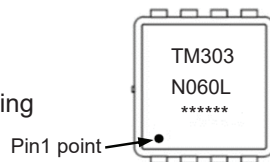
| Package | Tape Width (mm) | Pitch   |               | Reel Size |      | Per Reel Packing Quantity |
|---------|-----------------|---------|---------------|-----------|------|---------------------------|
|         |                 | mm      | inch          | mm        | inch |                           |
| DFN3030 | 12              | 8 ± 0.1 | 0.315 ± 0.004 | 330       | 13   | 5,000                     |

Marking information

" TM303N060L " = Part No.

" \*\*\*\*\* " = Date Code Marking

Font type: Arial



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